

18. (Once Amended) The manufacturing method of the film acoustic wave device according to claim 60, wherein the step of changing the pattern shape includes a step of changing the width of the upper electrode by the position at the wafer.

b 19. (Once Amended) The manufacturing method of the film acoustic wave device according to claim 60, wherein the step of forming the upper electrode forms a plurality of upper electrodes, and wherein the step of changing the pattern shape includes a step of changing the distance between the upper electrodes by the position at the wafer.

20. (Once Amended) The manufacturing method of film acoustic wave device according to claim 60, and wherein the step of forming the upper electrode further includes a step of connecting of the upper electrode to a bonding pad, and wherein the step of changing the pattern shape includes a step of changing a shape of the bonding pad by the position at the wafer.

b 23. (Once Amended) The manufacturing method of the film acoustic wave device according to claim 60, further comprising a step for setting a capacitor on the same semiconductor substrate as the film acoustic wave device, and wherein the step of changing the pattern

B² shape includes a step of changing a capacitance of the capacitor by the position at the wafer.

Please add a new claim as follows:

B³ 60. A manufacturing method of the film acoustic wave device comprising steps of:

(a) forming a bottom electrode on top of a wafer made of a semiconductor substrate;

(b) forming a piezoelectric thin film on top of the bottom electrode;

(c) forming an upper electrode on top of the piezoelectric thin film; and

(d) changing a pattern shape of the upper electrode formed on top of the piezoelectric thin film by the position at the wafer.
